D45C12 (PNP), D44C12 (NPN)

Complementary Silicon Power Transistor

The D45C12 and D44C12 are for general purpose driver or medium power output stages in CW or switching applications.

Features

- Low Collector–Emitter Saturation Voltage 0.5 V (Max)
- High f_t for Good Frequency Response
- Low Leakage Current
- Pb-Free Packages are Available*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V _{CEO}	80	Vdc
Collector-Emitter Voltage	VCES	90	Vdc
Emitter Base Voltage	V _{EB}	5.0	Vdc
Collector Current - Continuous Peak (Note 1)	I _C	4.0 6.0	Adc
Total Power Dissipation @ T _C = 25°C @ T _A = 25°C	P _D	30 1.67	W W/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to 150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	4.2	°C/W
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	75	°C/W
Maximum Lead Temperature for Soldering Purposes: 1/8 in from Case for 5 Sec	TL	275	°C

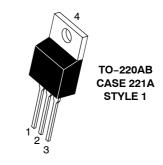
^{1.} Pulse Width \leq 6.0 ms, Duty Cycle \leq 50%.



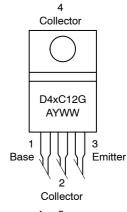
ON Semiconductor®

http://onsemi.com

4.0 AMPERE COMPLEMENTARY SILICON POWER TRANSISTORS 80 VOLTS



MARKING DIAGRAM & PIN ASSIGNMENT



x = 4 or 5

A = Assembly Location
Y = Year
WW = Work Week
G = Pb-Free Package

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

D45C12 (PNP), D44C12 (NPN)

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
DC Current Gain	h _{FE}			ı
$(V_{CE} = 1.0 \text{ Vdc}, I_{C} = 0.2 \text{ Adc})$		40	120	
$(V_{CE} = 1.0 \text{ Vdc}, I_{C} = 1.0 \text{ Adc})$		20	_	
$(V_{CE} = 1.0 \text{ Vdc}, I_{C} = 2.0 \text{ Adc})$		20	-	

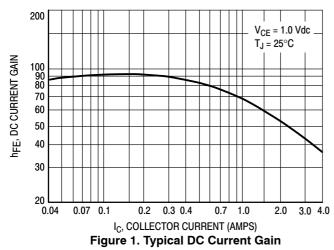
ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS	•		•		
Collector Cutoff Current (V _{CE} = Rated V _{CES} , V _{BE} = 0)	I _{CES}	-	-	0.1	μΑ
Emitter Cutoff Current (V _{EB} = 5.0 Vdc)	I _{EBO}	-	-	10	μΑ
ON CHARACTERISTICS					
Collector–Emitter Saturation Voltage (I _C = 1.0 Adc, I _B = 50 mAdc)	V _{CE(sat)}	-	0.135	0.5	Vdc
Base-Emitter Saturation Voltage (I _C = 1.0 Adc, I _B = 100 mAdc)	V _{BE(sat)}	-	0.85	1.3	Vdc
DYNAMIC CHARACTERISTICS		•			
Collector Capacitance (V _{CB} = 10 Vdc, f = 1.0 MHz)	C _{cb}	-	125	-	pF
Gain Bandwidth Product (I _C = 20 mA, V _{CE} = 4.0 Vdc, f = 20 MHz)	f _T	-	40	_	MHz
SWITCHING TIMES	·				
Delay and Rise Times (I _C = 1.0 Adc, I _{B1} = 0.1 Adc)	t _d + t _r	-	50	75	ns
Storage Time ($I_C = 1.0$ Adc, $I_{B1} = I_{B2} = 0.1$ Adc)	t _s	_	350	550	ns
Fall Time (I _C = 1.0 Adc, I _{B1} = I _{B2} = 0.1 Adc)	t _f	-	50	75	ns

ORDERING INFORMATION

Device	Package	Shipping [†]
D45C12	TO-220AB	
D45C12G	TO-220AB (Pb-Free)	50 Units / Rail
D44C12	TO-220AB	30 Offits / Hall
D44C12G	TO-220AB (Pb-Free)	

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.



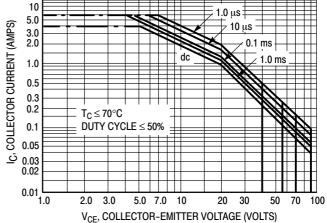
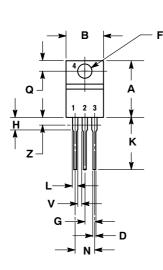


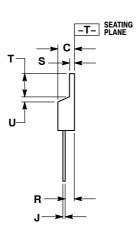
Figure 2. Maximum Rated Forward Bias
Safe Operating Area

D45C12 (PNP), D44C12 (NPN)

PACKAGE DIMENSIONS

TO-220 CASE 221A-09 **ISSUE AG**





NOTES

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: INCH.
- DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.570	0.620	14.48	15.75
В	0.380	0.405	9.66	10.28
С	0.160	0.190	4.07	4.82
D	0.025	0.036	0.64	0.91
F	0.142	0.161	3.61	4.09
G	0.095	0.105	2.42	2.66
Н	0.110	0.161	2.80	4.10
J	0.014	0.025	0.36	0.64
K	0.500	0.562	12.70	14.27
Г	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
Т	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
٧	0.045		1.15	
Z		0.080		2.04

STYLE 1:

BASE

- COLLECTOR
- **EMITTER**
- COLLECTOR

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BCR158WH6327XTSA1 NSBA114TDP6T5G NSBA143TF3T5G NSBA143ZF3T5G NSBC114EF3T5G NSBC114YF3T5G
NSBC123TF3T5G NSBC143TF3T5G NSVMUN2212T1G NSVMUN5111DW1T3G NSVMUN5314DW1T3G NSVUMC2NT1G
SMMUN2134LT1G SMUN2212T1G SMUN5235T1G SMUN5330DW1T1G SSVMUN5312DW1T2G 2SC3650-TD-E RN1303(TE85L,F)
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SMMUN2111LT3G SMMUN2113LT1G SMMUN2114LT1G SMMUN2211LT3G SMUN2214T3G SMUN5113DW1T1G
SMUN5335DW1T1G NSBA114YF3T5G NSBC114TF3T5G